

HIGH LEVEL LOGIC DIODE-TRANSISTOR MICROLOGIC®

INTEGRATED CIRCUITS COMPOSITE DATA SHEET

A FAIRCHILD COMPATIBLE CURRENT SINKING LOGIC PRODUCT

0°C TO 75°C TEMPERATURE RANGE

GENERAL DESCRIPTION — The Fairchild High Level Logic Diode-Transistor Micrologic® Integrated Circuit family (HLLDT μ L) consists of three high voltage, high threshold hex inverters which offer extremely good D.C. and A.C. Noise Immunity. These circuits are useful in applications involving a high noise environment or high voltage supply which prohibits the use of CCSL.

Interfacing from CCSL to HLLDT μ L is accomplished with the 9112, shifting from HLLDT μ L to CCSL is accomplished with the 9109. The 9112 can also be used to drive the μ M3700 MOS Multiplexer.

The circuits are fabricated within a silicon monolithic substrate using standard Fairchild Planar* and Epitaxial processes.

HLLDT μ L elements are available in the hermetically sealed ceramic Dual In-Line Package (DIP), designed for automated and low cost insertion techniques.

FEATURES

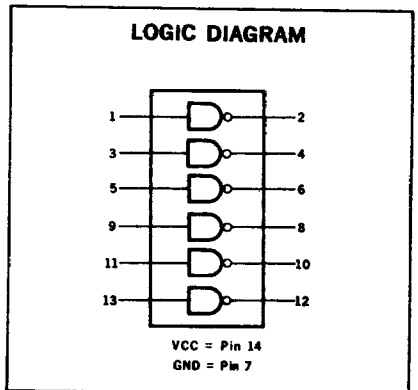
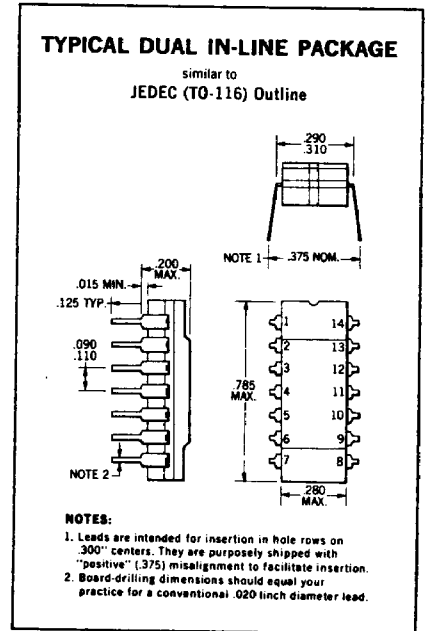
- High Voltage Operation . . . V_{CC} Range 12 to 20 V.
- Utilizes inexpensive external input diodes to facilitate a high density building block approach and very high Logic Fan-In where desired.
- High D.C. Noise Immunity . . . 6.5 V minimum
- High A.C. Noise Immunity . . . 10 V at 150 ns
- Interfaces with CCSL

ABSOLUTE MAXIMUM RATINGS (above which the reliability of the device may be impaired)

Storage Temperature	-65°C to +150°C
Operating Temperature	0°C to +75°C
V_{CC} Pin Potential to Gnd Pin	-0.5 V to +25 V
Output Current when output is low	40 mA
Input Current (9109, 9110)	10 mA
Output Voltage	25 V
Input Voltage (9112)	5.5 V

ORDERING INFORMATION

To order HLLDT μ L elements specify U6AXXX59X, where XXXX is the four-digit number denoting the specific element desired.



*Planar is a patented Fairchild process.

FAIRCHILD HLLDT μ L INTEGRATED CIRCUITS

ELECTRICAL CHARACTERISTICS

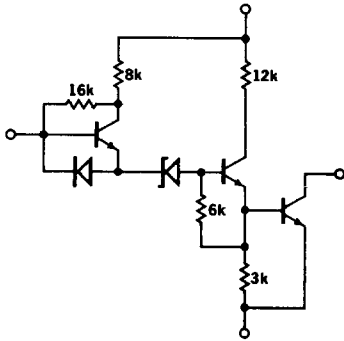
SYMBOL	CHARACTERISTIC	DEVICE	LIMITS						UNITS	CONDITIONS AND COMMENTS
			0°C		+25°C		+75°C			
			MIN.	MAX.	MIN.	TYP.	MAX.	MIN.		
V_{OH}	Output High Voltage	9110 9112	Note 2		Note 2		Note 2		Volts	$V_{CC} = 12\text{ V to }20\text{ V}$ $I_{OH} = -0.1\text{ mA}$ @ V_{IL}
I_{CEX}	Output Leakage Current	9109	75		1.0	75	75		μA	$V_{CC} = 20\text{ V}$ $V_{OH} = 20\text{ V}$ @ V_{IL}
V_{OL1}	Output Low Voltage	9109 9110 9112	0.5		0.25	0.5	0.5		Volts	$V_{CC} = 12\text{ V}$ $I_{OL} = 10\text{ mA}$ @ V_{IH}
V_{OL2}	Output Low Voltage	9109 9110 9112	1.0		0.5	1.0	1.0		Volts	$V_{CC} = 20\text{ V}$ $I_{OL} = 20\text{ mA}$ @ V_{IH}
V_{IL}	Input Low Voltage	9109	7.05		7.0		6.8		Volts	Input Low Threshold @ V_{OH}
		9110								
		9112	1.05		1.0		0.8			
V_{IH}	Input High Voltage	9109	8.6		8.5		8.4		Volts	Input High Threshold @ V_{OL}
		9110								
		9112	2.1		2.0		1.9			
I_F	Input Load Current	9109 9110 9112	-1.20		-0.80	-1.12	-1.12		mA	$V_{CC} = 20\text{ V}$, $V_F = 0.5\text{ V}$
I_{SC}	Output Short Circuit Current	9110	-17		-9.0	-16.3	-15.6		mA	$V_{CC} = 20\text{ V}$, $V_{IN} = 0\text{ V}$ $V_{OUT} = 0\text{ V}$
		9112	-2.4		-1.65	-2.3	-2.3			
I_{CEX}	Output Leakage Current	9110 9112	75		1.0	75	75		μA	$V_{CC} = 20\text{ V}$, $V_{OUT} = 20\text{ V}$ $V_{IN} = 0\text{ V}$
I_{PDH}	Input High Supply Current	9109			19	28			mA	$V_{CC} = 20\text{ V}$, Input Open
		9110								
		9112			22	34				
I_R	Input Leakage Current	9112			5.0		10		μA	$V_{CC} = 20\text{ V}$, $V_R = 4.0\text{ V}$
I_{max}	Ground Current	9109							mA	$V_{CC} = V_{OUT} = 25\text{ V}$, Inputs @ GND
		9110			15					
		9112								
t_{pd+}	Turn Off Delay	9109							ns	See Fig. 4
		9110			145	300				
		9112								
t_{pd-}	Turn On Delay	9109							ns	See Fig. 4
		9110			95	200				
		9112			30	125				
V_{TN}	"0" Level A.C. Noise Immunity	9110			7.0				Volts	See Fig. 5
V_{TP}	"1" Level A.C. Noise Immunity	9110			8.5				Volts	See Fig. 5

NOTES:

- (1) Tests on 9109, 9110 are performed with FDH6 input diodes.
- (2) MIN = $V_{CC} - 2.0\text{ V}$ for all temperature
TYP = $V_{CC} - 1.5\text{ V}$ for 25°C

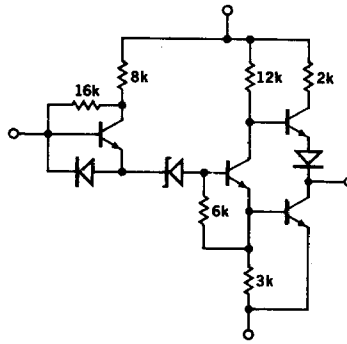
FAIRCHILD HLLDT μ L INTEGRATED CIRCUITS

Fig. 1a



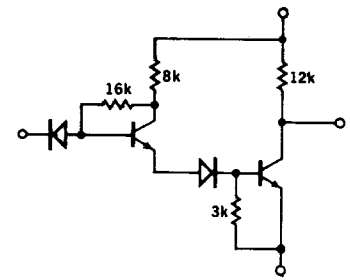
1/6 HLLDTL 9109
HLL → CCSL

Fig. 1b



1/6 HLLDTL 9110
HLL → HLL

Fig. 1c



1/6 HLLDTL 9112
CCSL → HLL

Fig. 2a

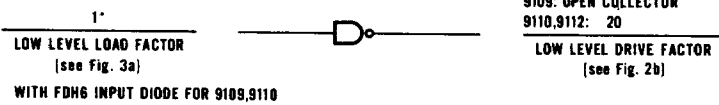


Fig. 2b
OUTPUT LOADS
(LOW LEVEL DRIVE FACTOR)
VERSUS SUPPLY VOLTAGE

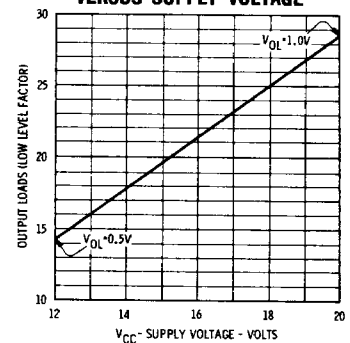


Fig. 3a

WORST CASE INPUT FORWARD CURRENT AND INPUT LOADS
VERSUS SUPPLY VOLTAGE

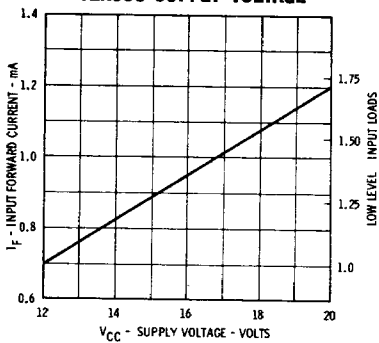


Fig. 3b

WORST CASE POWER DISSIPATION
VERSUS SUPPLY VOLTAGE
(PER GATE)

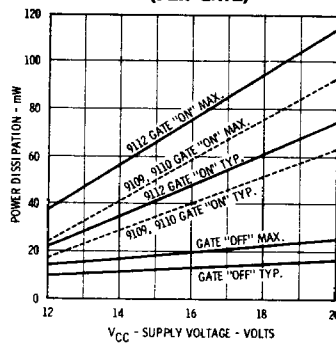


Fig. 3c

WORST CASE HIGH LEVEL
D.C. NOISE IMMUNITY

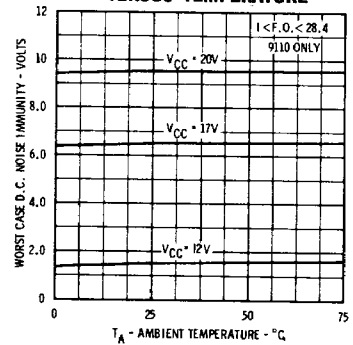


Fig. 3d

WORST CASE HIGH INPUT
THRESHOLD VOLTAGE

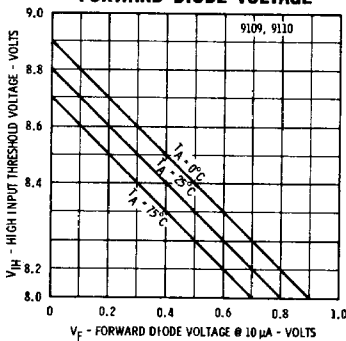


Fig. 3e

WORST CASE LOW THRESHOLD
VOLTAGE

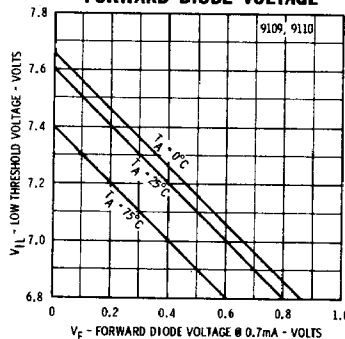


Fig. 3f

WORST CASE LOW LEVEL
D.C. NOISE IMMUNITY

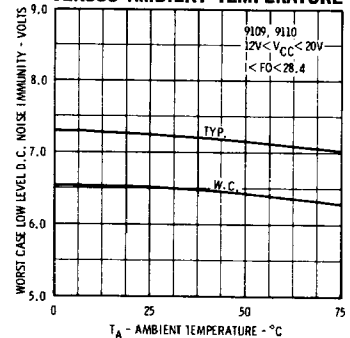


Fig. 3g
TURN OFF DELAY
VERSUS AMBIENT TEMPERATURE

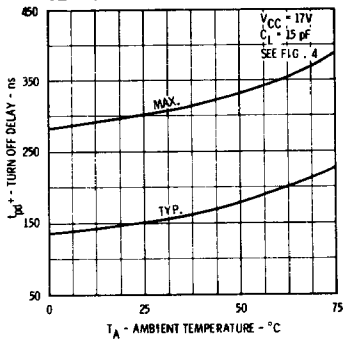


Fig. 3h
TURN ON DELAY
VERSUS AMBIENT TEMPERATURE

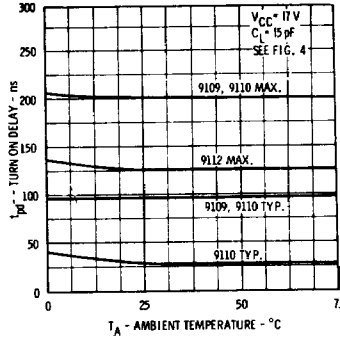


Fig. 3i
TYPICAL A.C. NOISE IMMUNITY
INPUT VOLTAGE VERSUS
PULSE WIDTH

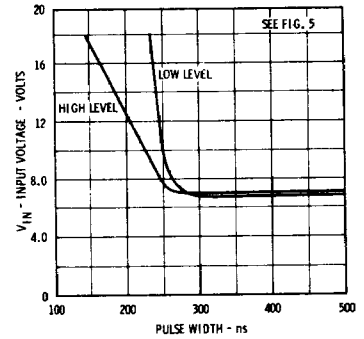
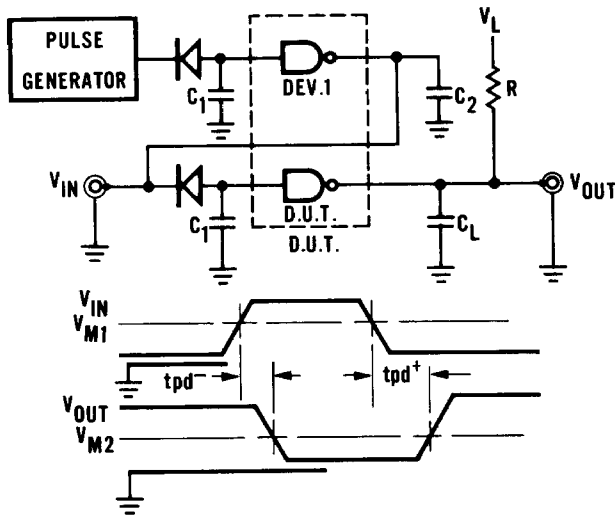


Fig. 4
SWITCHING TIME TEST CIRCUIT
AND WAVEFORMS



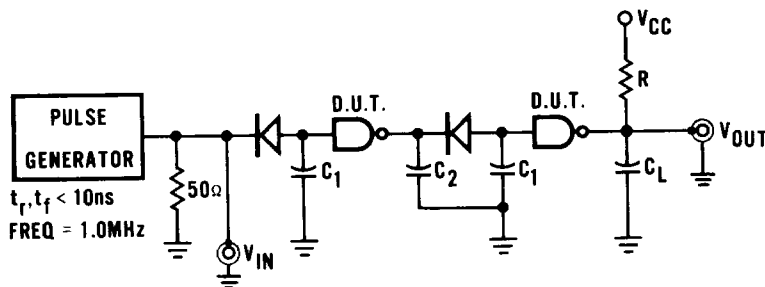
$C_1 = 5.0 \text{ pF}$ Includes all probe
 $C_2 = 10 \text{ pF}$ and jig capacitance
 $C_L = 15 \text{ pF}$

FDHG Input Diodes are used on 9109, 9110

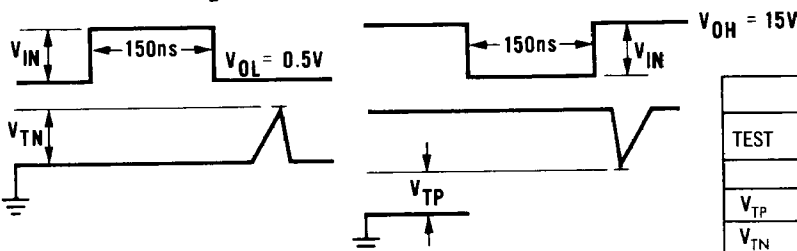
TEST CONDITIONS

D.U.T.	DEV. 1	V_{m1} (V)	V_{m2} (V)	V_L (V)	R_{tpd-}	R_{tpd+}
9109	9110	7.5	1.5	5.0	510 Ω	3.6 k
9110	9110	7.5	7.5	17.0	2.4 k	24 k
9112	932	1.5	7.5	17.0	2.4 k	24 k

Fig. 5
A.C. NOISE IMMUNITY TEST CIRCUIT



Unused inputs grounded
diodes are FDHG
 $C_1 = 5.0 \text{ pF}$ Includes jig and
 $C_2 = 10 \text{ pF}$ all probe capacitance
 $C_L = 15 \text{ pF}$



TEST CONDITIONS AND LIMITS

TEST	LIMIT		V_{CC} (Volts)	R (k Ω)	T_A ($^{\circ}$ C)	V_{IN} (Volts)
	MIN.	MAX.				
V_{TP}	8.5 V		17	24	25	10
V_{TN}		7.0 V	17	2.4	25	10

APPLICATIONS:

Fig. 6—CCSL INTERFACING

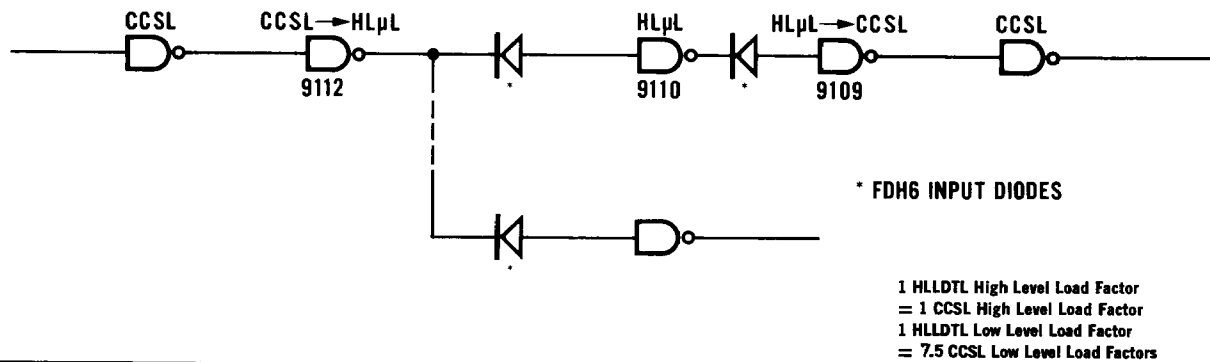


Fig. 7—LAMP DRIVER

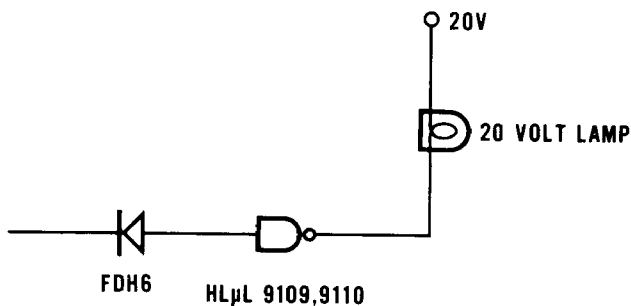
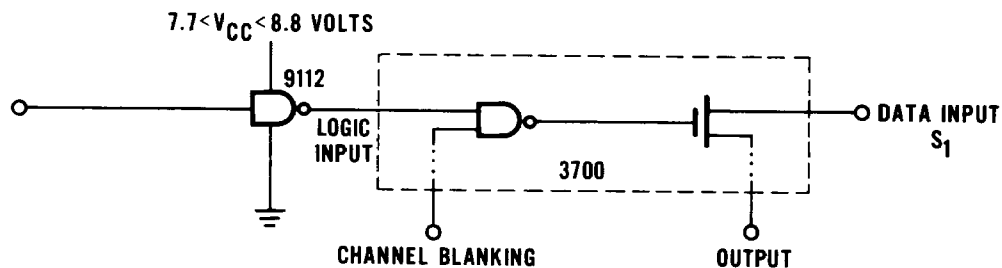
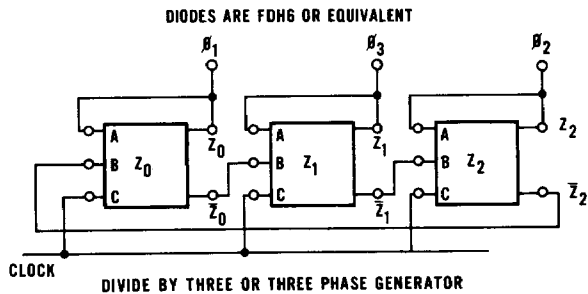


FIG. 8—DRIVING MOS3700 MULTIPLEXER OR EQUIVALENT



Output Levels : min "1" level = $V_{CC} - 1.5 V$
 : max "0" level = 0.2 V

Fig. 9—SEQUENTIAL COUNTER



ϕ_1	ϕ_3	ϕ_2	Clock
1	0	0	0
1	0	1	1
0	0	1	0
0	1	1	1
0	1	0	0
1	1	0	1

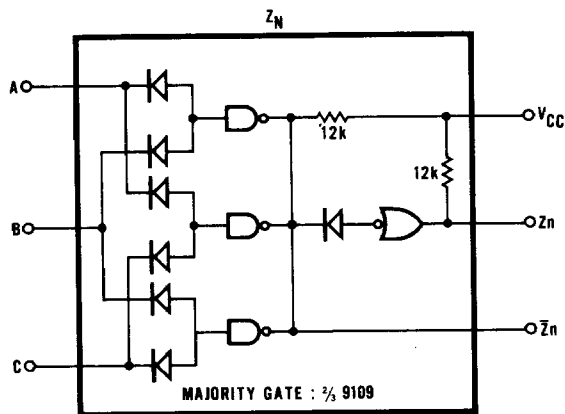
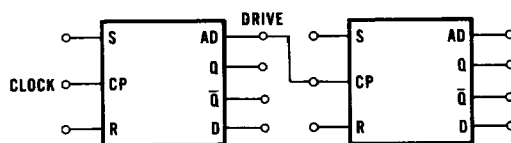
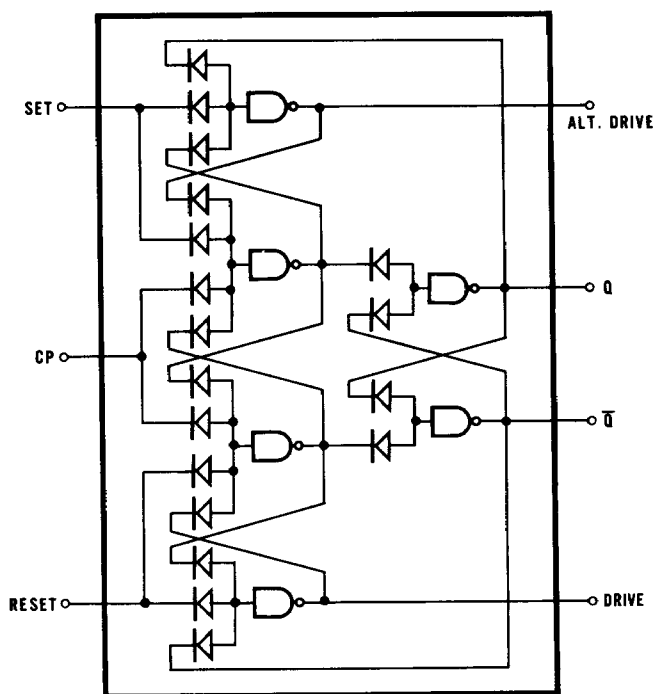
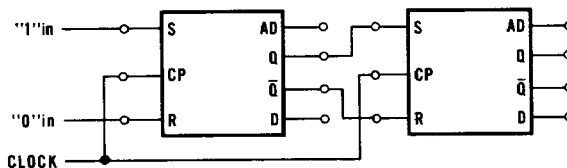


Fig. 10—JK FLIP FLOP



TOGGLE MODE



SHIFT MODE

DIODES ARE FDH6 OR EQUIVALENT

J	K	Q_{n+1}
L	H	L
L	L	Q_n
H	H	\bar{Q}_n
H	L	H